

RJK03M9DNS

Silicon N Channel Power MOS FET Power Switching

R07DS0775EJ0120 Rev.1.20 May 29, 2012

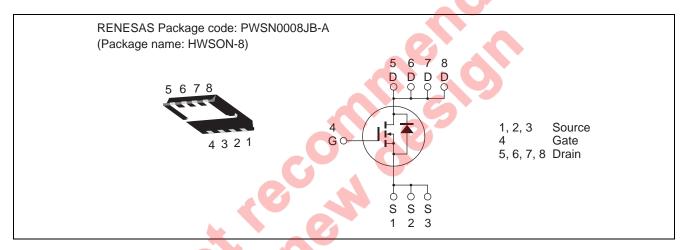
Features

- High speed switching
- Capable of 4.5 V gate drive
- Low drive current
- High density mounting
- Low on-resistance

 $R_{DS(on)}\!=9.2~\text{m}\Omega$ typ. (at $V_{GS}\!=10~\text{V})$

- Pb-free
- Halogen-free

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit	
Drain to source voltage	V_{DSS}	30	V	
Gate to source voltage	V_{GSS}	±20	V	
Drain current	I _D	14	A	
Drain peak current	I _{D(pulse)} Note1	56	A	
Body-drain diode reverse drain current	I _{DR}	14	A	
Avalanche current	I _{AP} Note 2	7	A	
Avalanche energy	E _{AS} Note 2	4.9	mJ	
Channel dissipation	Pch Note3	10	W	
Channel to case thermal impedance	θch-c Note3	12.5	°C/W	
Channel temperature	Tch	150	°C	
Storage temperature	Tstg	-55 to +150	°C	

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Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

- 2. Value at Tch = 25°C, Rg \geq 50 Ω
- 3. Tc = 25°C

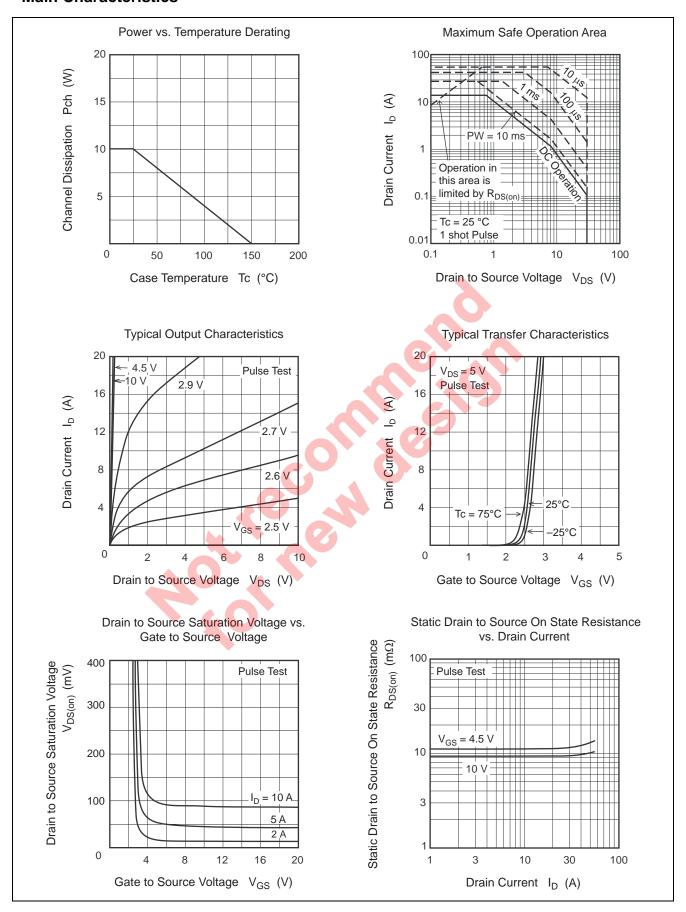
Electrical Characteristics

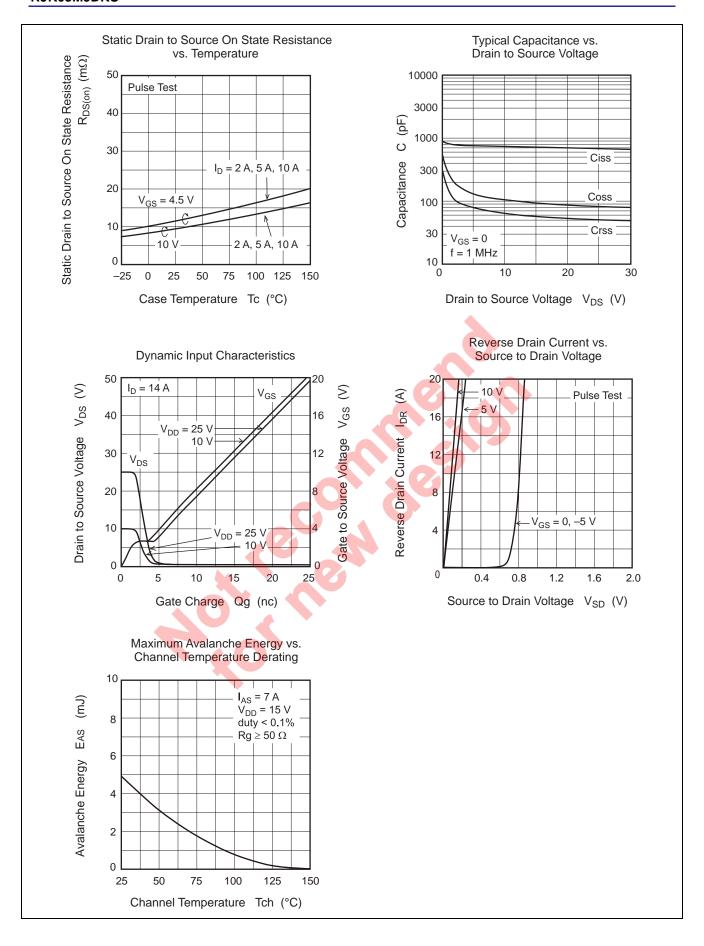
 $(Ta = 25^{\circ}C)$

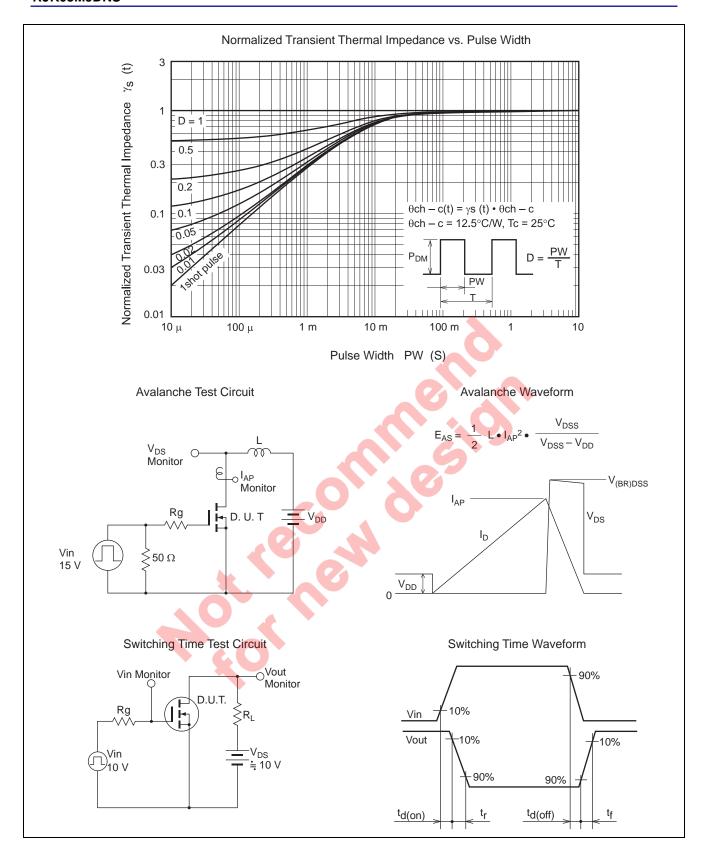
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	30 — 1.2 — — —	 9.2 11.5 32	± 0.5 1 2.5 11.1	V μΑ μΑ V mΩ	$\begin{split} I_D &= 10 \text{ mA, } V_{GS} = 0 \\ V_{GS} &= \pm 20 \text{ V, } V_{DS} = 0 \\ V_{DS} &= 24 \text{ V, } V_{GS} = 0 \\ V_{DS} &= 10 \text{ V, } I_D = 1 \text{ mA} \\ I_D &= 7 \text{ A, } V_{GS} = 10 \text{ V}^{\text{Note4}} \end{split}$			
		11.5	1 2.5 11.1	μA V mΩ	$V_{DS} = 24 \text{ V}, V_{GS} = 0$ $V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$			
Gate to source cutoff voltage Static drain to source on state resistance Forward transfer admittance Input capacitance Ciss Output capacitance Coss Reverse transfer capacitance Gate Resistance Total gate charge Gate to source charge Gate to drain charge Turn-on delay time Rise time Turn-off delay time Fall time Repson RDS(on) RD		11.5	2.5 11.1	V mΩ	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$			
Static drain to source on state resistance RDS(on) Forward transfer admittance Ipts Input capacitance Output capacitance Ciss Output capacitance Coss Reverse transfer capacitance Crss Gate Resistance Total gate charge Qate to source charge Qate to drain charge Turn-on delay time Rise time Turn-off delay time Fall time RDS(on) RDS(on) RDS(on) RDS(on) RDS(on) Ross Quits Crss Quits Quits Ad(on) Rise time tr Turn-off delay time tf	1.2 — — — —	11.5	11.1	mΩ				
resistance Forward transfer admittance Ipfs Input capacitance Output capacitance Coss Reverse transfer capacitance Gate Resistance Total gate charge Gate to source charge Qg Gate to drain charge Turn-on delay time Rise time Turn-off delay time Fall time Rocion Ross Ross Ross Ross Coss Rg Coss Rg Qg Qg Qg Gate to drain charge Qgd Turn-on delay time to to to to to to to to to t	_ _ _ _	11.5			$I_D = 7 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note4}}$			
Forward transfer admittance $ y_{fs} $ Input capacitance Ciss Output capacitance Coss Reverse transfer capacitance Crss Gate Resistance Rg Total gate charge Qg Gate to source charge Qgs Gate to drain charge Qgd Turn-on delay time $t_{d(on)}$ Rise time t_{r} Turn-off delay time $t_{d(off)}$ Fall time t_{r}	<u> </u>		15					
Input capacitance Output capacitance Coss Reverse transfer capacitance Crss Gate Resistance Total gate charge Gate to source charge Qg Gate to drain charge Turn-on delay time Rise time Turn-off delay time Turn-off delay time Tell time Coss Rg Rg Rg Rg Rg Rg Rg Rg Rg	_	32		$m\Omega$	$I_D = 7 \text{ A}, V_{GS} = 4.5 \text{ V}^{\text{Note4}}$			
Output capacitance Coss Reverse transfer capacitance Crss Gate Resistance Rg Total gate charge Qg Gate to source charge Qgs Gate to drain charge Qgd Turn-on delay time t _{d(on)} Rise time t _r Turn-off delay time t _{d(off)} Fall time t _f	_		_	S	$I_D = 7$ A, $V_{DS} = 5$ V Note4			
$ \begin{array}{cccccccccccccccccccccccccccccccccccc$		700	980	рF	V _{DS} = 10 V			
$ \begin{array}{cccc} \text{Gate Resistance} & \text{Rg} \\ \text{Total gate charge} & \text{Qg} \\ \text{Gate to source charge} & \text{Qgs} \\ \text{Gate to drain charge} & \text{Qgd} \\ \text{Turn-on delay time} & t_{d(on)} \\ \text{Rise time} & t_r \\ \text{Turn-off delay time} & t_{d(off)} \\ \text{Fall time} & t_f \\ \end{array} $	_	120	_	рF	$V_{GS} = 0$			
	_	65	_	рF	f = 1 MHz			
$ \begin{array}{cccc} \text{Gate to source charge} & \text{Qgs} \\ \text{Gate to drain charge} & \text{Qgd} \\ \text{Turn-on delay time} & t_{d(\text{on})} \\ \text{Rise time} & t_{r} \\ \text{Turn-off delay time} & t_{d(\text{off})} \\ \text{Fall time} & t_{f} \\ \end{array} $	_	1.6	3.2	Ω				
	_	6.0	_	nC	V _{DD} = 10 V			
	_	2.0	_	nC	$V_{GS} = 4.5 \text{ V}$			
	_	1.8	_	nC	I _D = 14 A			
	_	2.4	_	ns	$V_{GS} = 10 \text{ V}, I_D = 7 \text{ A}$			
Fall time t _f	_	2.4		ns	$V_{DD} \cong 10 \text{ V}$			
	_	11.2		ns	$R_L = 1.43 \Omega$			
	_	3.2		ns	$Rg = 4.7 \Omega$			
Body–drain diode forward voltage V _{DF}	_	0.84	1.09	V	$I_F = 14 \text{ A}, V_{GS} = 0^{\text{Note4}}$			
Body-drain diode reverse recovery t _{rr}	_	7.4		ns	I _F = 14 A, V _{GS} = 0			
time	_			<u> </u>	di _F / dt = 500 A/ μs			
Notes: 4. Pulse test								

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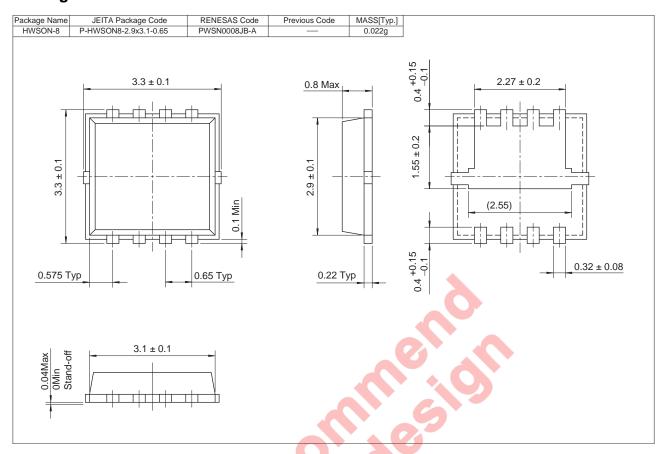
Main Characteristics







Package Dimensions



Ordering Information

Orderable Part Number	Quantity		Shipping Container
RJK03M9DNS-00-J5	5000 pcs	Taping	

Note: The symbol of 2nd "-" is occasionally presented as "#".

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